

AMENDMENTS TO THE SPECIFICATION

Please add the following new paragraph prior to the paragraph beginning on line 5:

-- This application is a continuation application of U.S. Serial No. 10/045,711,
filed January 14, 2002.--

Please add the following new paragraph after the paragraph ending on line 16 of Page 1:

--This application claims benefit of U.S. Provisional Application No. 60/261,292,
filed January 12, 2001.--

Please replace the paragraph beginning at Page 2, line 11, with the following rewritten paragraph:

--Prior art inductor structures used in RF and microwave circuits are commonly isolated from ground using ~~SiO₂~~ SiO₂ which has a dielectric constant (k) of 4 to 4.2. Prior art ~~capacitors~~ inductors may be passivated with a polymer dielectric (e.g. ~~Polyimide~~ Polyimide) which has a dielectric constant (k) or about 2.9.--

Please replace the paragraph beginning at Page 3, line 9, with the following rewritten paragraph:

--Prior art capacitor structures used in RF and microwave circuits are commonly isolated from ground using SiO₂ which has a dielectric constant (k) of 4 to 4.2, or another material with still larger k. The capacitors may be passivated with a polymer dielectric (e.g. ~~Polyimide~~ Polyimide) which has a dielectric constant (k) or about 2.9.--

Please replace the paragraph beginning at Page 16, line 13, with the following rewritten paragraph:

--Referring to Figure 6, on a substrate 32 60 are deposited patterned metal conductors ~~40 and 50~~ 68 which are formed within a low-k dielectric, ~~44 and 38~~ 61. Atop the dielectric 38 61 is a second layer of low-k dielectric 65 and atop the low-k dielectric 65 is a masking/cmp-stop layer, 72 63. Within layers 65 and 63 the metal conductors, 62, are formed. In the preferred structure, said masking/cmp-stop layer, 72 63 is comprised of the thin film form of the SiCOH dielectric having a thickness from 20-100 nm, and preferably 30-60 nm. Atop the masking/cmp-stop layer 72 63, and the metal conductors, 40 62, is the “post-CMP Cap” layer, 6[[2]]4. In the preferred structure, said post CMP-cap layer is an amorphous alloy of Si, C, H or Si, N, C H. Atop the “post-CMP Cap” layer, 64, is a third layer of low-k dielectric 65 and atop the low-k dielectric is a masking/cmp-stop layer, 67. Metal conductors, 66, are formed within the layers 65 and 67.--

Please replace the paragraph beginning at Page 17, line 1, with the following rewritten paragraph:

-- The SiCOH dielectric layer 72 65 and 61, in Figure 6 has the preferred atomic composition H 30-35%, C 13-17%, Si 20-26%, O 25-32%. At this composition, and in the 20-100 nm range of thickness, the measured current versus electric field curve is similar to that shown in Figure 9 below, and a breakdown field of greater than 6 MV/cm is measured (see Figure 9), and a dielectric constant of less than 3.5. More generally, the composition may be H 25-55%, C 10-40%, Si 10-30%, O 10-35%. Optionally, the

composition is not uniform throughout the film thickness, and a “graded” composition is used for example to improve adhesion at an interface.--